

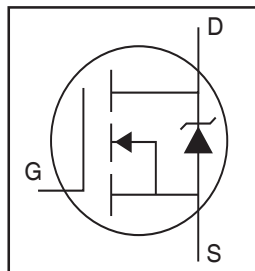
Features

- Advanced Process Technology
- Ultra Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to T_{jmax}
- Lead-Free, RoHS Compliant
- Automotive Qualified *

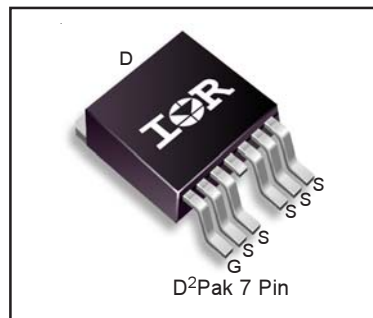
Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications such as Electric Power Steering, Battery Switch, SMPS and other heavy loads.

HEXFET® Power MOSFET



V_{DSS}	40V
$R_{DS(on)}$ typ.	0.90mΩ
max.	1.25mΩ
I_D (Silicon Limited)	400A ①
I_D (Package Limited)	240A



G	D	S
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRFS3004-7P	D²Pak 7 Pin	Tube	50	AUIRFS3004-7P
		Tape and Reel Left	800	AUIRFS3004-7TRL

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

Symbol	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	400①	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	280①	
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V (Wire Bond Limited)	240	
I_{DM}	Pulsed Drain Current ②	1610	
P_D @ $T_C = 25^\circ\text{C}$	Maximum Power Dissipation	380	W
	Linear Derating Factor	2.5	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy (Thermally limited) ③	290	mJ
I_{AR}	Avalanche Current ②	See Fig. 14, 15, 22a, 22b	A
E_{AR}	Repetitive Avalanche Energy ②		mJ
dv/dt	Peak Diode Recovery ④	2.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)		

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑤ ⑥	—	0.40	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑤	—	40	

HEXFET® is a registered trademark of International Rectifier.

*Qualification standards can be found at <http://www.irf.com/>

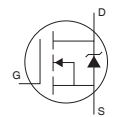
Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	40	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.038	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 5mA$ ②
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.90	1.25	m Ω	$V_{GS} = 10V, I_D = 195A$ ⑤
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	1300	—	—	S	$V_{DS} = 10V, I_D = 195A$
R_G	Internal Gate Resistance	—	2.0	—	Ω	
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 40V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 40V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$

Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge	—	160	240	nC	$I_D = 180A$
Q_{gs}	Gate-to-Source Charge	—	42	—		$V_{DS} = 20V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	65	—		$V_{GS} = 10V$ ⑤
Q_{sync}	Total Gate Charge Sync. ($Q_g - Q_{gd}$)	—	95	—		$I_D = 180A, V_{DS} = 0V, V_{GS} = 10V$
$t_{d(on)}$	Turn-On Delay Time	—	23	—	ns	$V_{DD} = 26V$
t_r	Rise Time	—	240	—		$I_D = 240A$
$t_{d(off)}$	Turn-Off Delay Time	—	91	—		$R_G = 2.7\Omega$
t_f	Fall Time	—	160	—		$V_{GS} = 10V$ ⑤
C_{iss}	Input Capacitance	—	9130	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	2020	—		$V_{DS} = 25V$
C_{riss}	Reverse Transfer Capacitance	—	990	—		$f = 1.0\text{ MHz}$, See Fig. 5
$C_{oss\text{ eff. (ER)}}$	Effective Output Capacitance (Energy Related) ⑦	—	2590	—		$V_{GS} = 0V, V_{DS} = 0V$ to $32V$ ⑦, See Fig. 11
$C_{oss\text{ eff. (TR)}}$	Effective Output Capacitance (Time Related) ⑥	—	2650	—		$V_{GS} = 0V, V_{DS} = 0V$ to $32V$ ⑥

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	400	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ②	—	—	1610	A	
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 195A, V_{GS} = 0V$ ⑤
t_{rr}	Reverse Recovery Time	—	49	—	ns	$T_J = 25^\circ\text{C}$ $V_R = 34V$,
		—	51	—		$T_J = 125^\circ\text{C}$ $I_F = 240A$
Q_{rr}	Reverse Recovery Charge	—	37	—	nC	$T_J = 25^\circ\text{C}$ $di/dt = 100A/\mu s$ ⑤
		—	41	—		$T_J = 125^\circ\text{C}$
I_{RRM}	Reverse Recovery Current	—	3.2	—	A	$T_J = 25^\circ\text{C}$
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

- ① Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 240A. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements. (Refer to AN-1140)
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 0.01mH$
 $R_G = 25\Omega$, $I_{AS} = 240A$, $V_{GS} = 10V$. Part not recommended for use above this value.

- ④ $I_{SD} \leq 240A$, $di/dt \leq 740A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$.
- ⑤ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ⑥ $C_{oss\text{ eff. (TR)}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑦ $C_{oss\text{ eff. (ER)}}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑧ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑨ R_{θ} is measured at T_J approximately 90°C .
- ⑩ $R_{\theta JC}$ value shown is at time zero.

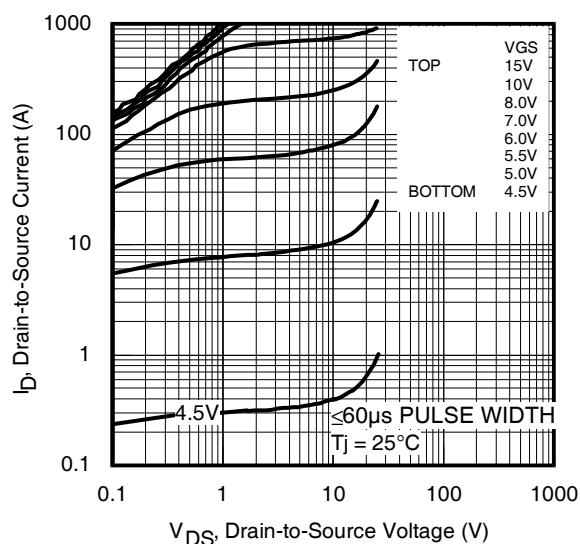
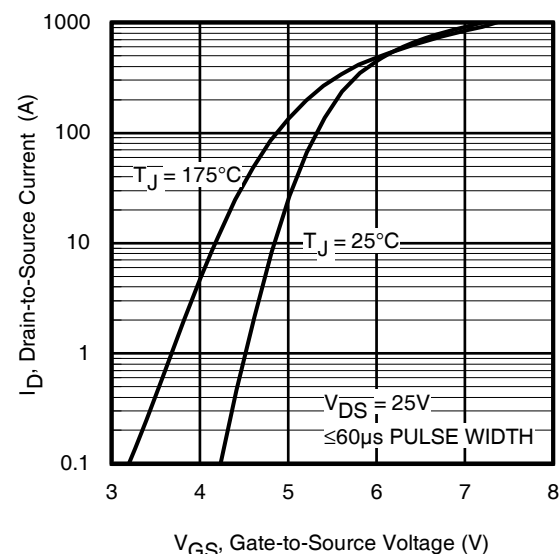
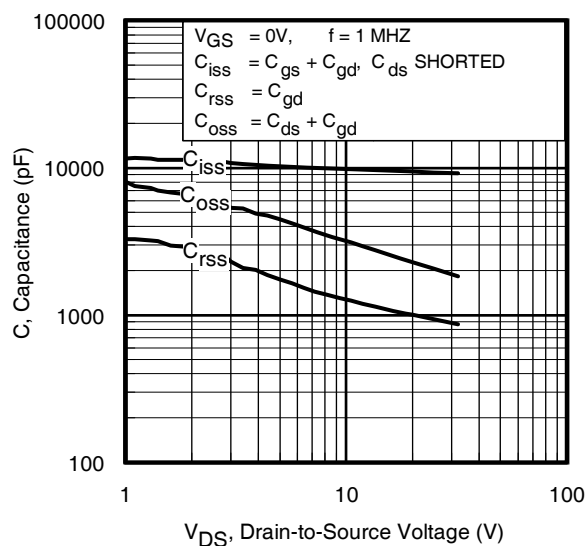
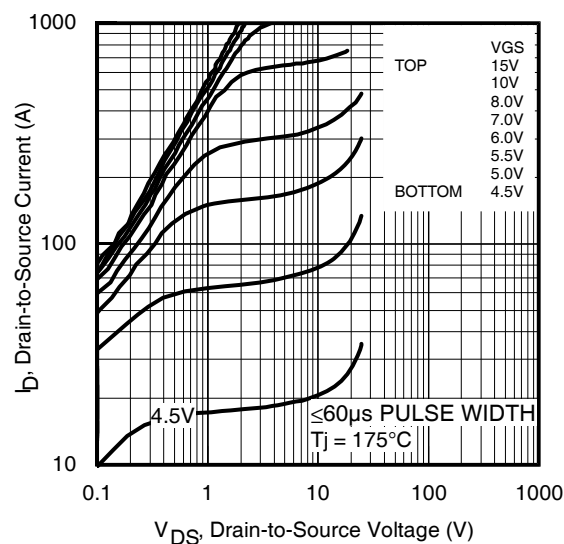
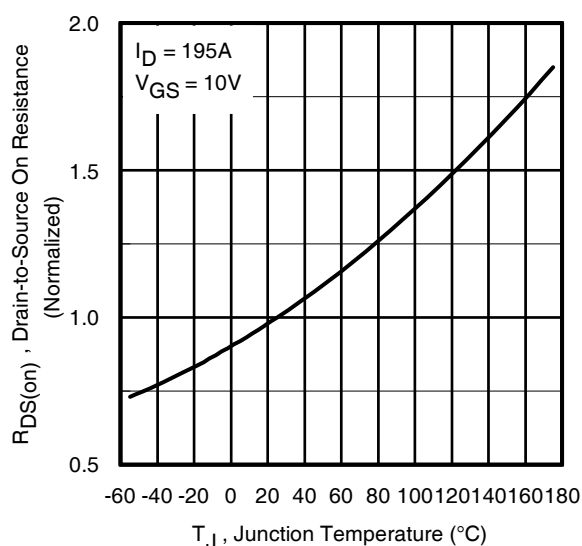
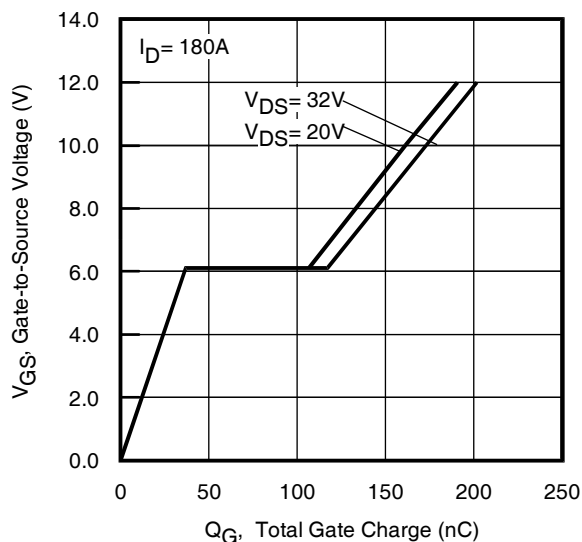
Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101) ^{††}	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
		D ² PAK - 7 Pin	MSL1
ESD	Machine Model	Class M4 (+/- 800V) ^{†††} AEC-Q101-002	
	Human Body Model	Class H3A (+/- 6000V) ^{†††} AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 2000V) ^{†††} AEC-Q101-005	
RoHS Compliant		Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

^{††} Exceptions (if any) to AEC-Q101 requirements are noted in the qualification report.

^{†††} Highest passing voltage.


Fig 1. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

Fig 2. Typical Output Characteristics

Fig 4. Normalized On-Resistance vs. Temperature

Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

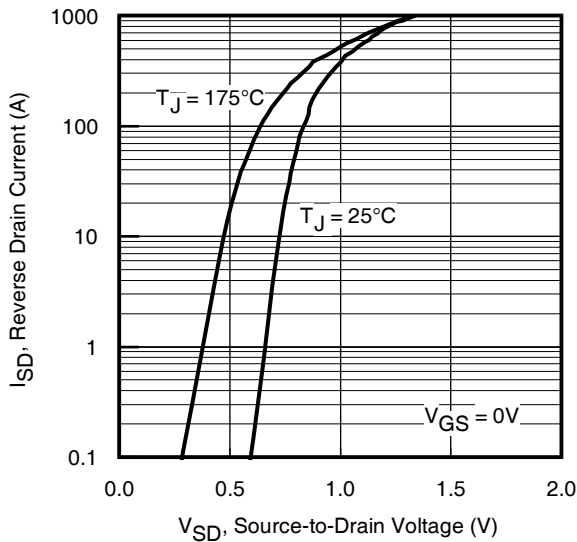


Fig 7. Typical Source-Drain Diode Forward Voltage

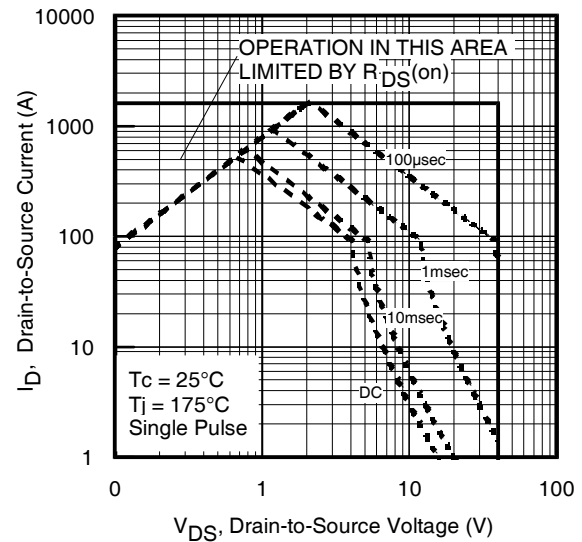


Fig 8. Maximum Safe Operating Area

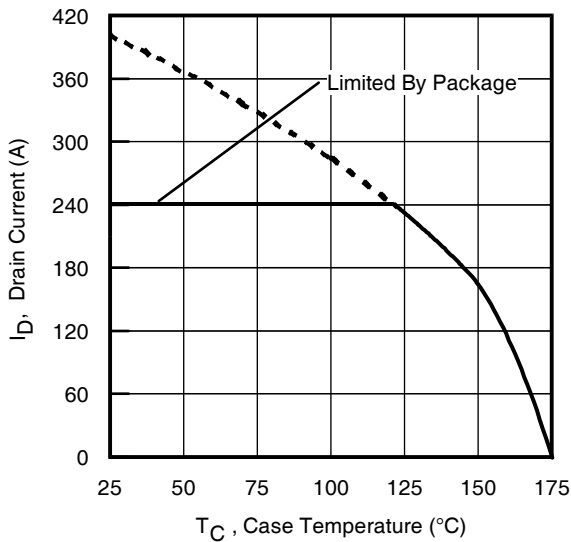


Fig 9. Maximum Drain Current vs. Case Temperature

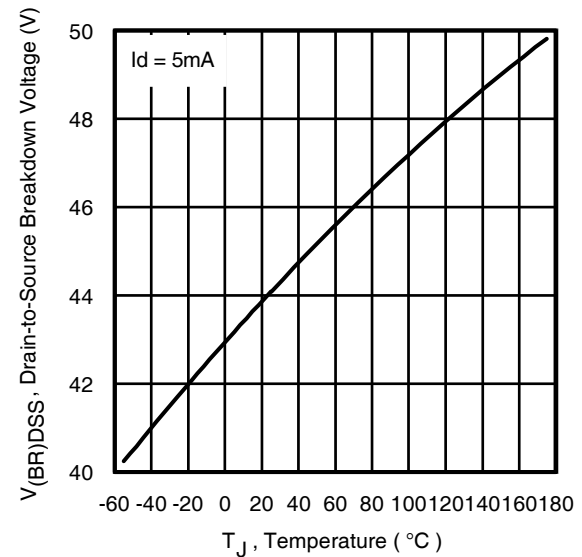


Fig 10. Drain-to-Source Breakdown Voltage

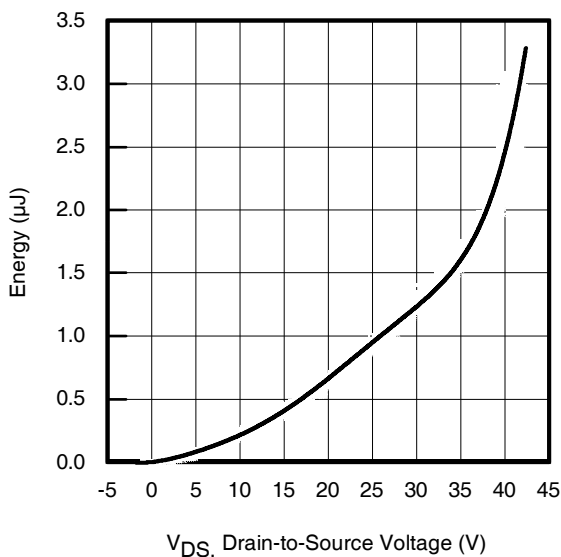


Fig 11. Typical C_{OSS} Stored Energy

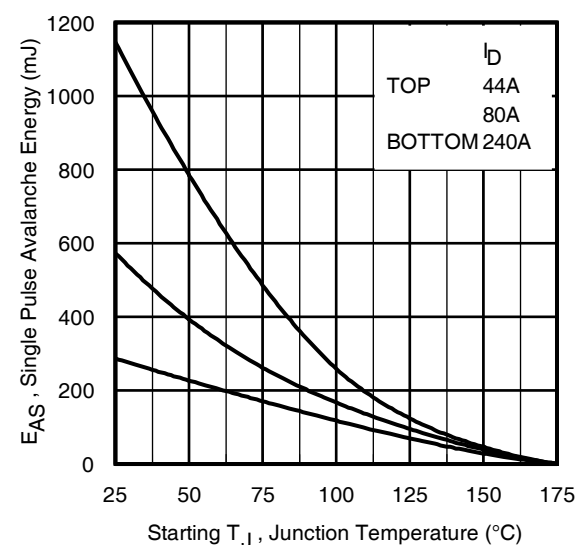
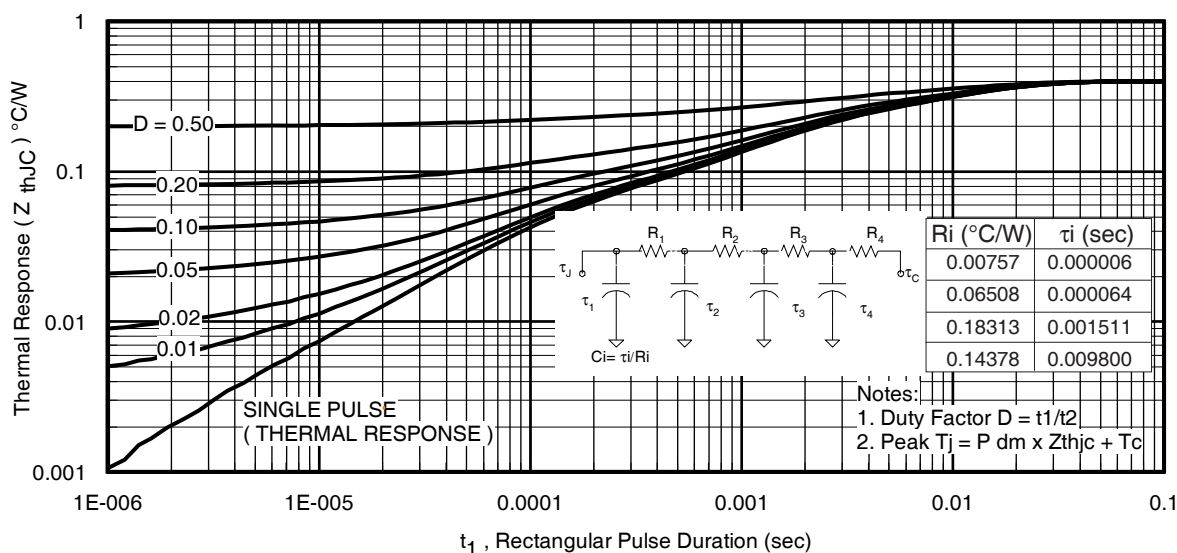
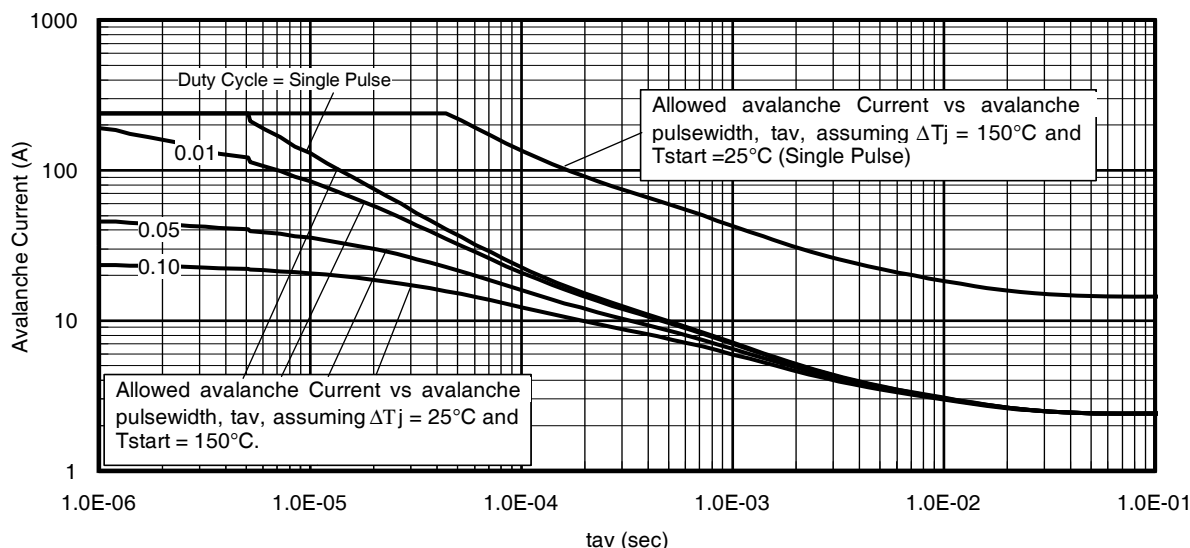
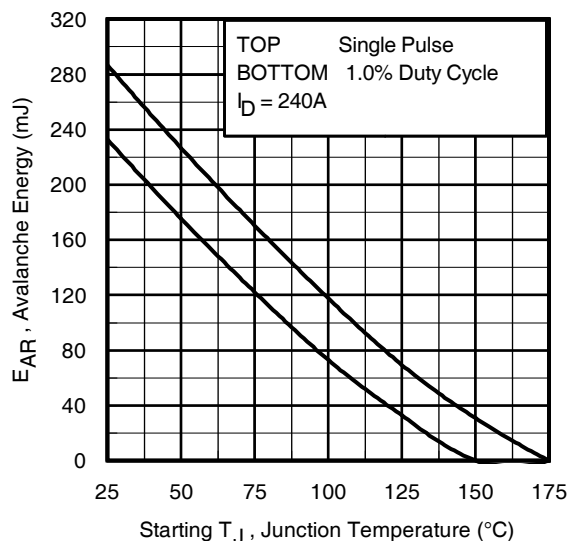


Fig 12. Maximum Avalanche Energy vs. Drain Current


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Fig 14. Typical Avalanche Current vs. Pulsewidth


Notes on Repetitive Avalanche Curves , Figures 14, 15:
 (For further info, see AN-1005 at www.irf.com)

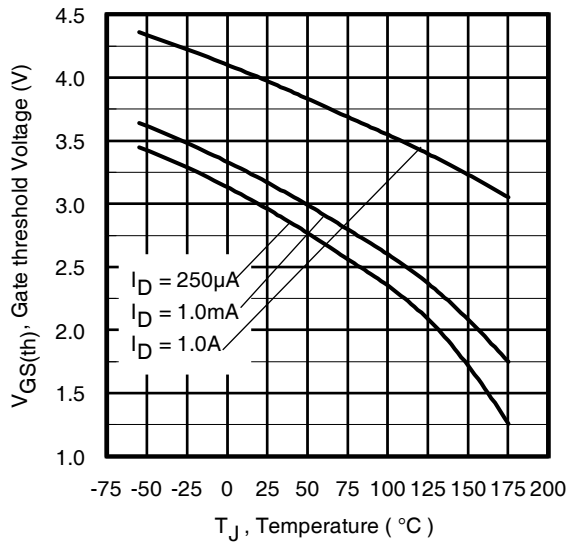
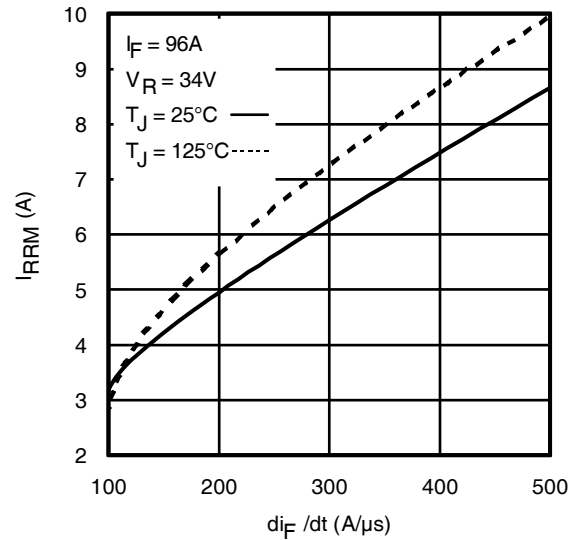
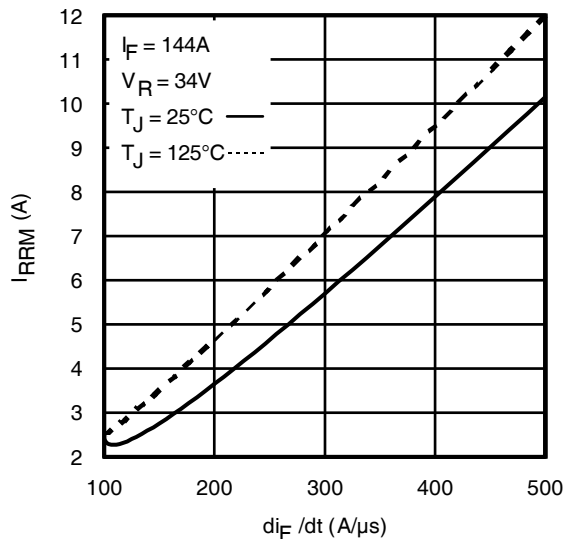
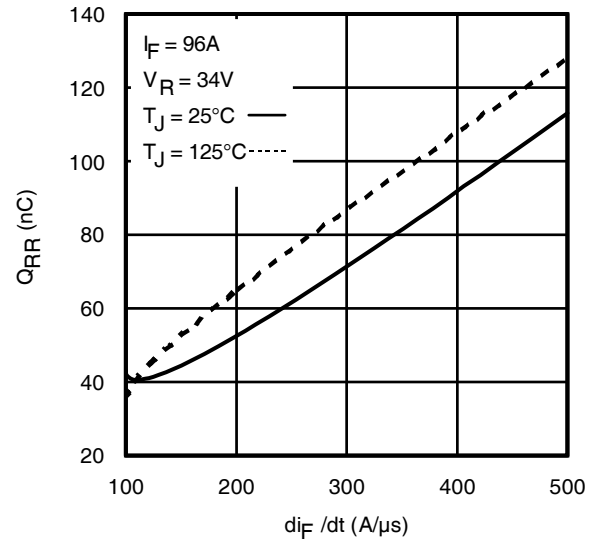
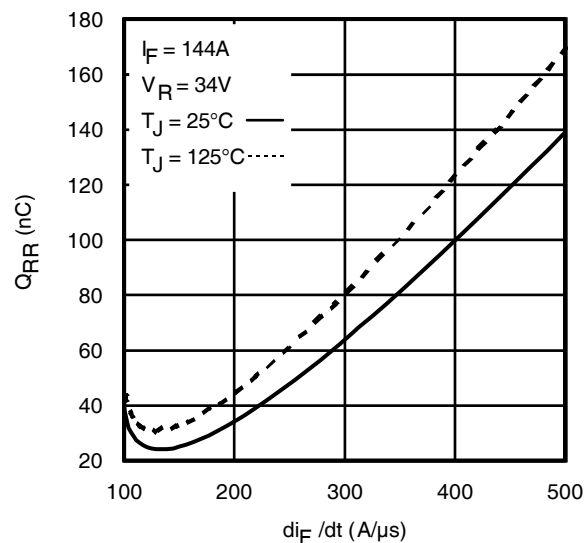
1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 16a, 16b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

Fig 15. Maximum Avalanche Energy vs. Temperature


Fig 16. Threshold Voltage vs. Temperature

Fig. 17 - Typical Recovery Current vs. di_F/dt

Fig. 18 - Typical Recovery Current vs. di_F/dt

Fig. 19 - Typical Stored Charge vs. di_F/dt

Fig. 20 - Typical Stored Charge vs. di_F/dt

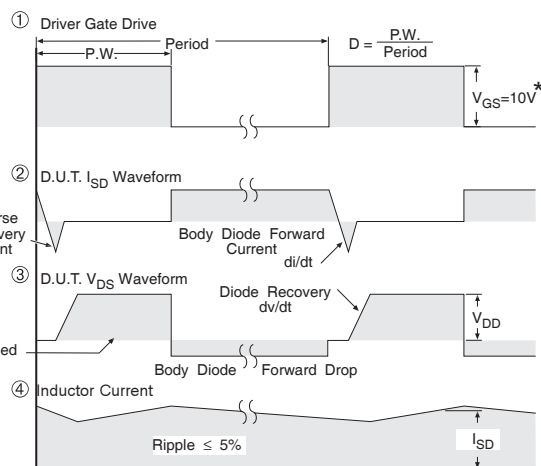
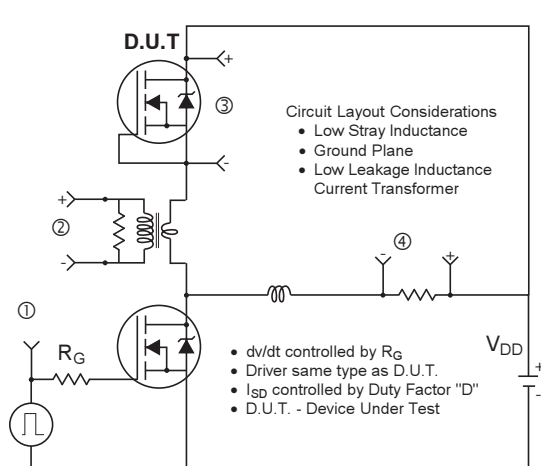


Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

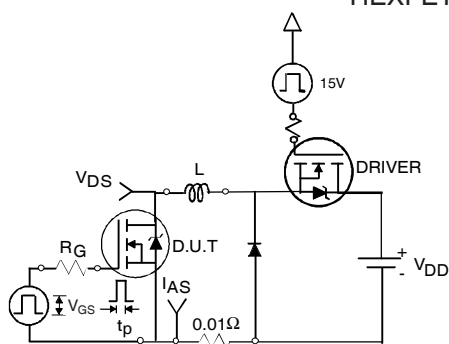


Fig 22a. Unclamped Inductive Test Circuit

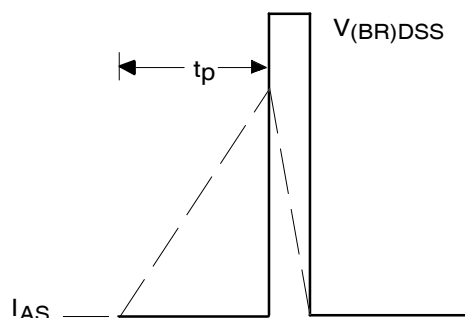


Fig 22b. Unclamped Inductive Waveforms

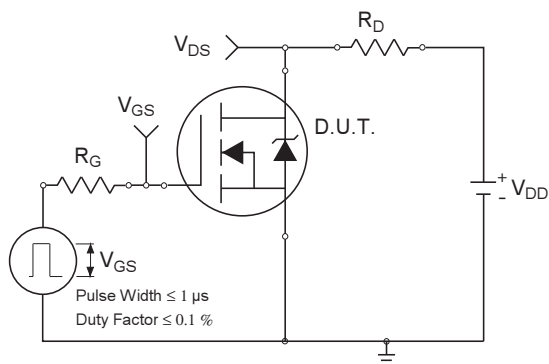


Fig 23a. Switching Time Test Circuit

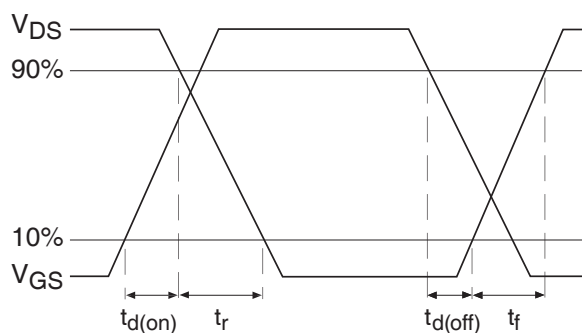


Fig 23b. Switching Time Waveforms

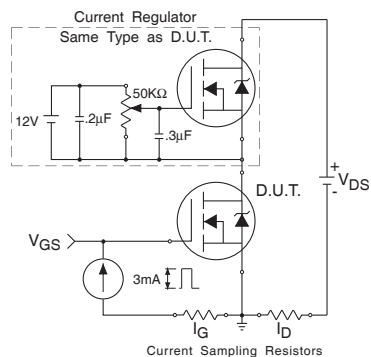


Fig 24a. Gate Charge Test Circuit

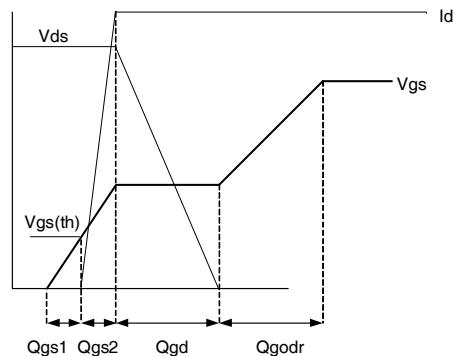
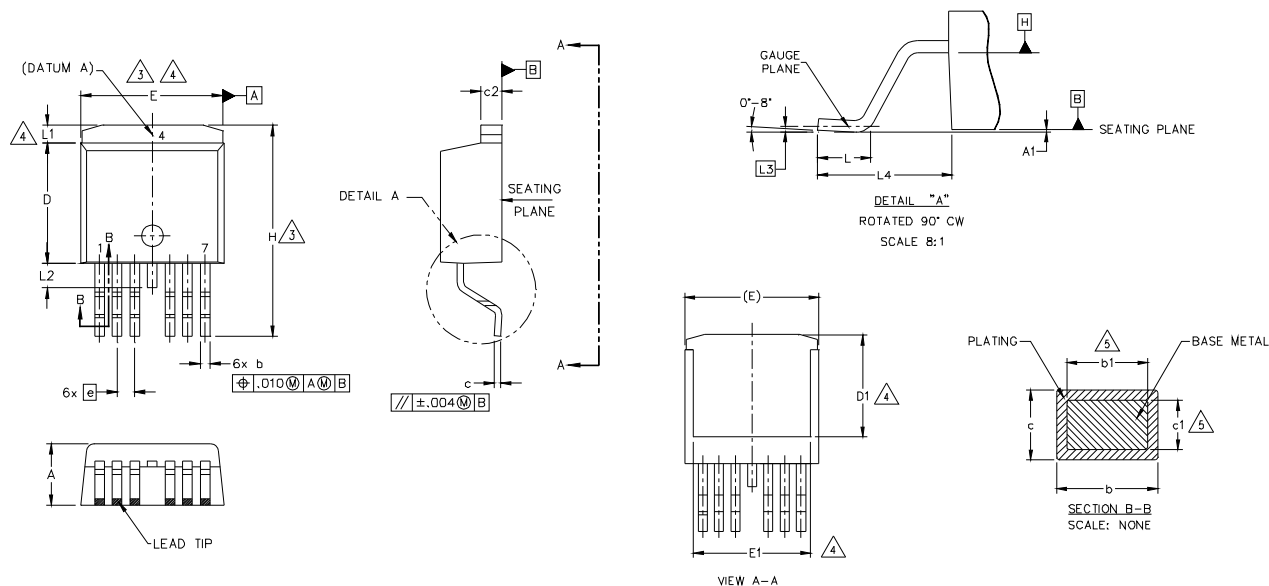


Fig 24b. Gate Charge Waveform

D²Pak - 7 Pin Package Outline

Dimensions are shown in millimeters (inches)



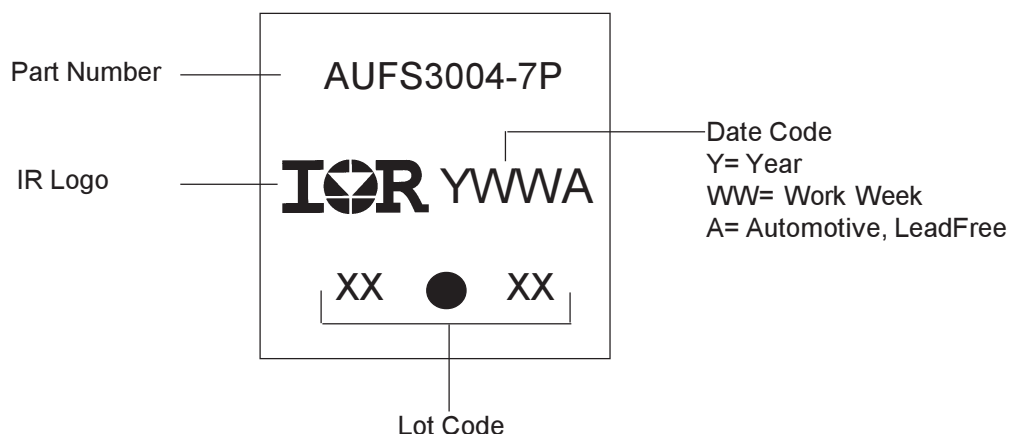
SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	5
A1	—	0.254	—	.010	
b	0.51	0.99	.020	.036	
b1	0.51	0.89	.020	.032	
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	3
D	8.38	9.65	.330	.380	
D1	6.86	—	.270	—	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	—	.245	—	4
e	1.27 BSC		.050 BSC		4
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	—	1.68	—	.066	
L2	—	1.78	—	.070	
L3	0.25 BSC		.010 BSC		
L4	4.78	5.28	.188	.208	

NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
7. CONTROLLING DIMENSION: INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263CB.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

D²Pak - 7 Pin Part Marking Information

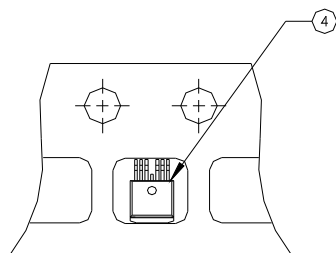


D²Pak - 7 Pin Tape and Reel

NOTES, TAPE & REEL, LABELLING:

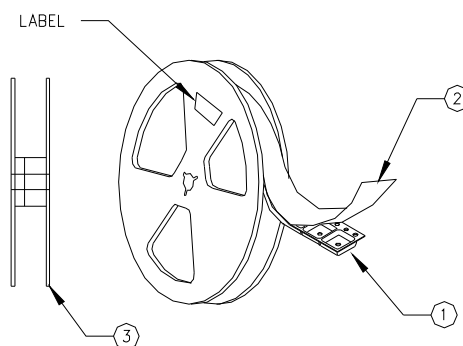
1. TAPE AND REEL.

- 1.1 REEL SIZE 13 INCH DIAMETER.
- 1.2 EACH REEL CONTAINING 800 DEVICES.
- 1.3 THERE SHALL BE A MINIMUM OF 42 SEALED POCKETS CONTAINED IN THE LEADER AND A MINIMUM OF 15 SEALED POCKETS IN THE TRAILER.
- 1.4 PEEL STRENGTH MUST CONFORM TO THE SPEC. NO. 71-9667.
- 1.5 PART ORIENTATION SHALL BE AS SHOWN BELOW.
- 1.6 REEL MAY CONTAIN A MAXIMUM OF TWO UNIQUE LOT CODE/DATE CODE COMBINATIONS. REWORKED REELS MAY CONTAIN A MAXIMUM OF THREE UNIQUE LOT CODE/DATE CODE COMBINATIONS. HOWEVER, THE LOT CODES AND DATE CODES WITH THEIR RESPECTIVE QUANTITIES SHALL APPEAR ON THE BAR CODE LABEL FOR THE AFFECTED REEL.



2. LABELLING (REEL AND SHIPPING BAG).

- 2.1 CUST. PART NUMBER (BAR CODE): IRFXXXXSTRL-7P
- 2.2 CUST. PART NUMBER (TEXT CODE): IRFXXXXSTRL-7P
- 2.3 I.R. PART NUMBER: IRFXXXXSTRL-7P
- 2.4 QUANTITY:
- 2.5 VENDOR CODE: IR
- 2.6 LOT CODE:
- 2.7 DATE CODE:



Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

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For technical support, please contact IR’s Technical Assistance Center
<http://www.irf.com/technical-info/>

WORLD HEADQUARTERS:
 101 N. Sepulveda Blvd., El Segundo, California 90245
 Tel: (310) 252-7105

Revision History

Date	Comments
3/4/2015	<ul style="list-style-type: none"> • Updated datasheet based on new IR corporate template . • Updated part marking from "AUS3004-7P" to "AUIRFS3004-7P" on page 10.